

600V High and Low Side Driver

PRODUCT SUMMARY

V_{OFFSET} 600 V max.
I_{O+}/- 2.5 A / 3 A
V_{OUT} 7 V - 20 V
t_{on/off} (typ.) 170ns / 170ns

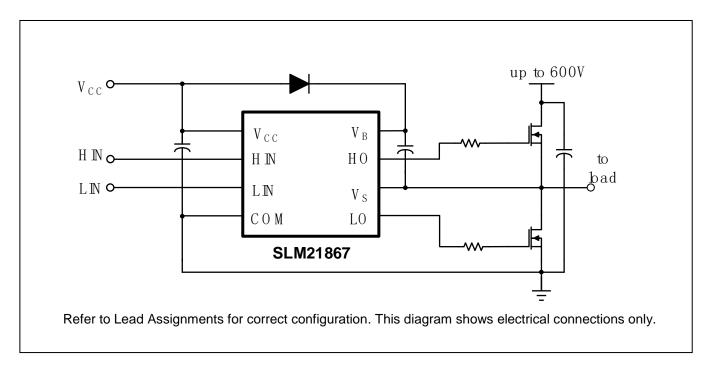
GENERAL DESCRIPTION

The SLM21867 is a high voltage, high speed power MOSFET and IGBT drivers with independent highlow-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3 V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600 V.

FEATURES

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Low V_{CC} operation
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 7 V to 20 V
- Undervoltage lockout for both channels
- 3.3 V, and 5 V logic compatible
- CMOS Schmitt-triggered inputs with pull-down
- Matched propagation delay for both channels
- Outputs in phase with inputs
- RoHS compliant
- SOP8 package

TYPICAL APPLICATION CIRCUIT





PIN CONFIGURATION

Package	Pin Configuration (Top View)
	1 V _{CC} V _B 8
SOP8	2 HIN HO 7
	3 LIN V _s 6
	4 COM LO 5

PIN DESCRIPTION

No.	Pin	Description
1	Vcc	Low-side and logic fixed supply
2	HIN	Logic input for high-side gate driver output (HO), in phase
3	LIN	Logic input for low-side gate driver output (LO), in phase
4	COM	Low-side return
5	LO	Low-side gate drive output
6	Vs	High-side floating supply return
7	НО	High-side gate drive output
8	V _B	High-side floating supply

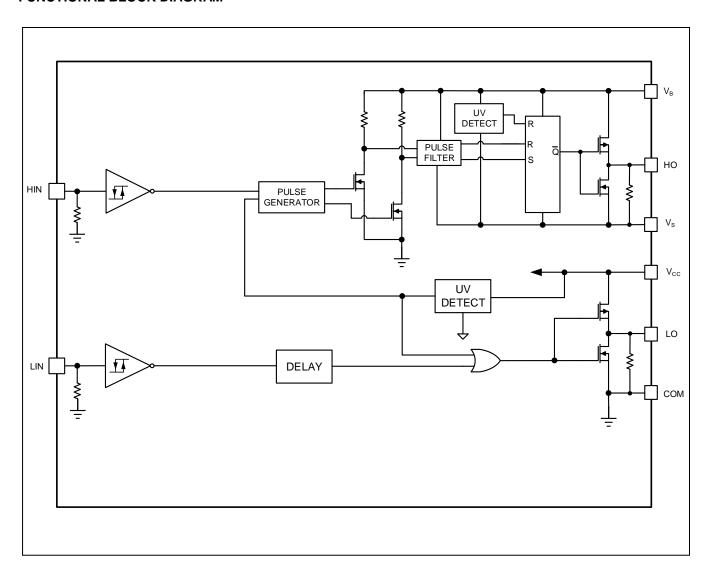
ORDERING INFORMATION

Industrial Range: -40°C to +125°C

Order Part No.	Package	QTY
SLM21867CA-DG	SOP8, Pb-Free	2500/Reel



FUNCTIONAL BLOCK DIAGRAM





ABSOLUTE MAXIMUM RATINGS

Symbol	Definition	Min.	Max.	Units
V _B	High-side floating absolute voltage	-0.3	625	
Vs	High-side floating supply offset voltage	V _B - 25	V _B + 0.3	
V _{HO}	High-side floating output voltage	Vs - 0.3	V _B + 0.3	,,
Vcc	Low-side and logic fixed supply voltage	-0.3	25	V
V _{LO}	Low-side output voltage	-0.3	Vcc + 0.3	
Vin	Logic input voltage (HIN & LIN)	-0.3	Vcc + 0.3	
dV _S /dt	Allowable offset supply voltage transient		50	V/ns
P _D	Package power dissipation @ T _A ≤ +25°C		0.625	W
θја	Thermal resistance, junction to ambient		200	°C/W
ΤJ	Junction temperature		150	
Ts	Storage temperature	-55	150	°C
T∟	Lead temperature (soldering, 10 seconds)		300	

Note: Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

RECOMMENDED OPERATION CONDITIONS

Symbol	Definition	Min.	Max.	Units
V _B	High-side floating absolute voltage	Vs + 7	Vs + 20	
Vs	High-side floating supply offset voltage	Note 1	600	
V _{но}	High-side floating output voltage	Vs	V _B	V
Vcc	Low-side and logic fixed supply voltage	7	20	V
VLO	Low-side output voltage	0	Vcc	
VIN	Logic input voltage (HIN & LIN)	COM	Vcc	
TA	Ambient temperature	- 40	125	°C

Note1: The input/output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at a 15 V differential.



DYNAMIC ELECTRICAL CHARACTERISTICS

 V_{BIAS} (V_{CC} , V_{BS}) = 15 V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
ton	Turn-on propagation delay	Vs = 0 V		170	250	
t _{off}	Turn-off propagation delay	Vs = 0 V		170	250	
tr	Turn-on rise time			8	16	ns
tf	Turn-off fall time			5	10	
MT	Delay matching, HS & LS turn-on/off				35	

STATIC ELECTRICAL CHARACTERISTICS

 V_{BIAS} (V_{CC} , V_{BS}) = 15 V and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} , and I_{IN} parameters are referenced to COM and are applicable to all logic input leads: HIN and LIN. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
VIH	Logic "1" input voltage	V _{CC} = 7 V to 20V	2.5			
V _{IL}	Logic "0" input voltage	100 110 201			0.8	V
Vон	High level output voltage, V _{BIAS} - V _O	I _O = 20 mA		0.08	0.2	v
V _{OL}	Low level output voltage, Vo	10 – 23 11111		0.07	0.15	
ILK	Offset supply leakage current	V _B = V _S = 600 V			50	
I _{QBS}	Quiescent V _{BS} supply current	V _{IN} = 0 V	20	60	100	
Iqcc	Quiescent V _{CC} supply current	V IIV — 0 V	200	290	400	μΑ
I _{IN+}	Logic "1" input bias current	HIN=LIN = 5V		30	70	
I _{IN} -	Logic "0" input bias current	HIN=LIN= 0V			5	
V _{BSUV+}	V _{BS} supply undervoltage positive going threshold		5.65	6.25	6.85	V
V _{BSUV} -	V _{BS} supply undervoltage negative going threshold		5.15	5.75	6.35	v
Vccuv+	Vcc supply undervoltage positive going threshold		5.65	6.25	6.85	V
V _{CCUV} -	V _{CC} supply undervoltage negative going threshold		5.15	5.75	6.35	·
l _{O+}	Output high short circuit pulsed current	V_{O} = 0 V, V_{IN} = Logic "1", PW \leq 10 µs	1.5	2.5		А
l _O -	Output low short circuit pulsed current	$V_0 = 15 \text{ V}, V_{IN} = \text{Logic "0"},$ $PW \le 10 \mu\text{s}$	2.0	3.0		, ,



SWITCHING AND TIMING RELATIONSHIPS

The relationships between the input and output signals of the SLM21867 are illustrated below in Figure 1, Figure 2. These figures show the definitions of several timing parameters (i.e., t_{on} , t_{off} , t_{r} , and t_{f}) associated with this device.

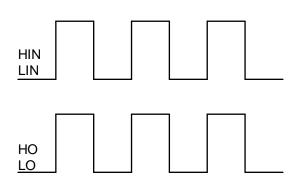


Figure 1. Input/Output Timing Diagram

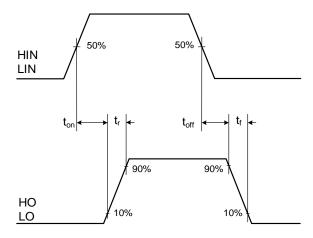


Figure 2. Switching Time Waveform

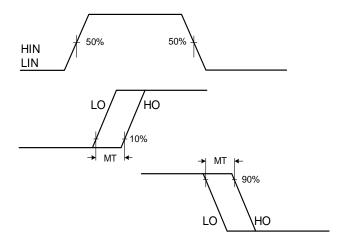
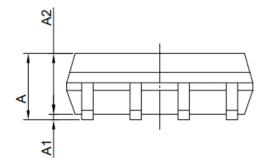
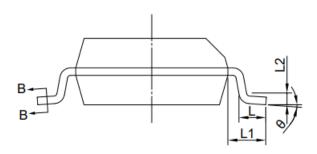


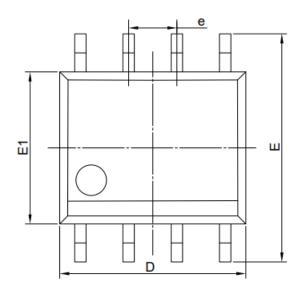
Figure 3. Delay Matching Waveform

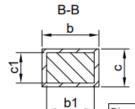


PACKAGE CASE OUTLINES









MIN NOM MAX			
-	-	1.75	
0.1	-	0.25	
1.25	-	-	
0.4	0.835	1.27	
-	1.04	-	
-	0.25	-	
0	-	8	
0.31	-	0.51	
0.28	-	0.48	
0.1	-	0.25	
0.1	-	0.25	
-	4.9	-	
-	6	-	
-	3.9	-	
1.27 BSC			
Unit : mm			
	- 0.1 1.25 0.4 - 0 0.31 0.28 0.1 0.1		

Figure 4. SOP8 Outline Dimensions



REVISION HISTORY

Note: page numbers for previous revisions may differ from page numbers in current version

Page or Item	Subjects (major changes since previous revision)		
Rev 0.1 datasheet, 201	9-9-1		
Whole document	Draft datasheet released		
Rev 0.2 datasheet, 202	0-1-14		
Page 2	Change order information		
Page 7	Add part marking information		
Rev 1.0 datasheet, 202	1-7-20		
Whole datasheet	Update the Logo		
Page 2	Removed the order part No. SLM21867CA-TG in the ordering information		
Page 3	Updated the Functional Block Diagram		
Page 4 Remove the PDIP-8 package information.			
	Updated the Vcc min voltage from 10V to 7V in the Recommended Operation Conditions.		
Page 5	Updated the t _r and t _f value in the Dynamic Electrical Characteristics.		
Update the $V_{\text{OH}},\ V_{\text{OL}},\ I_{\text{QBS}},\ I_{\text{IN+}}$, $I_{\text{O+}}$ and $I_{\text{O-}}$ value in the Static Ele Characteristics.			
Rev 1.1 datasheet, 202	2-7-26		
Page 7	Change the package name from SOIC-8 to SOP8 and update the package case outlines		
Rev 1.2 Datasheet, 202	22-12-29		
Page 7	SOP8 Outline Dimensions Update		